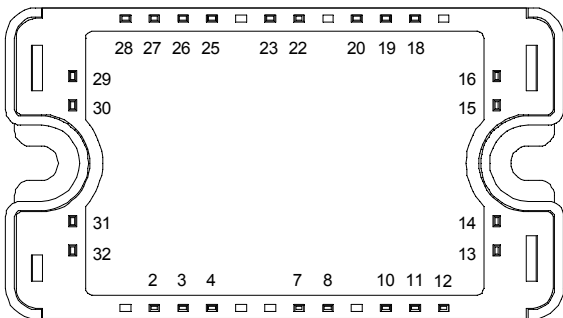
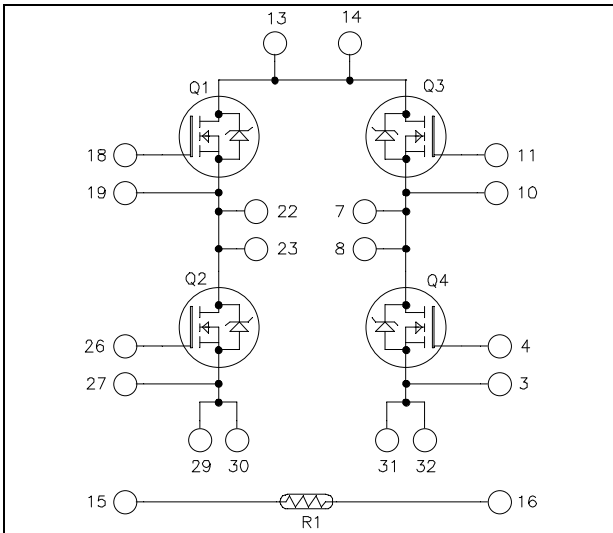


## Full bridge MOSFET Power Module

$V_{DSS} = 1000V$   
 $R_{DSon} = 460m\Omega \text{ typ @ } T_j = 25^\circ C$   
 $I_D = 19A \text{ @ } T_c = 25^\circ C$



All multiple inputs and outputs must be shorted together  
 Example: 13/14 ; 29/30 ; 22/23 ...

### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Power MOS 8™ Fast FREDFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- Very low stray inductance
  - Symmetrical design
- Kelvin source for easy drive
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	1000	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	19
		$T_c = 80^\circ C$	14
$I_{DM}$	Pulsed Drain current	120	
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	552	m $\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	357
$I_{AR}$	Avalanche current (repetitive and non repetitive)	16	A

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 1000\text{V}$ $V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$		250	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 16\text{A}$		460	552	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	3	4	5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			$\pm 100$	$\text{nA}$

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		6800		$\text{pF}$
$C_{oss}$	Output Capacitance			715		
$C_{rss}$	Reverse Transfer Capacitance			92		
$Q_g$	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 500\text{V}$ $I_D = 16\text{A}$		260		$\text{nC}$
$Q_{gs}$	Gate – Source Charge			46		
$Q_{gd}$	Gate – Drain Charge			125		
$T_{d(on)}$	Turn-on Delay Time	<b>Resistive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 15\text{V}$ $V_{Bus} = 667\text{V}$ $I_D = 16\text{A}$ $R_G = 2.2\Omega$		36		$\text{ns}$
$T_r$	Rise Time			37		
$T_{d(off)}$	Turn-off Delay Time			140		
$T_f$	Fall Time			35		

**Source - Drain diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_S$	Continuous Source current (Body diode)		$T_c = 25^\circ\text{C}$		19	A
			$T_c = 80^\circ\text{C}$		14	
$V_{SD}$	Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -16\text{A}$			1	V
$dv/dt$	Peak Diode Recovery ①				25	$\text{V/ns}$
$t_{rr}$	Reverse Recovery Time	$I_S = -16\text{A}$ $V_R = 100\text{V}$ $di/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		290	$\text{ns}$
			$T_j = 125^\circ\text{C}$		600	
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	1.3		$\mu\text{C}$
			$T_j = 125^\circ\text{C}$	3.5		

 ①  $dv/dt$  numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq -16\text{A}$     $di/dt \leq 1000\text{A}/\mu\text{s}$     $V_{DD} \leq 667\text{V}$     $T_j \leq 125^\circ\text{C}$

**Thermal and package characteristics**

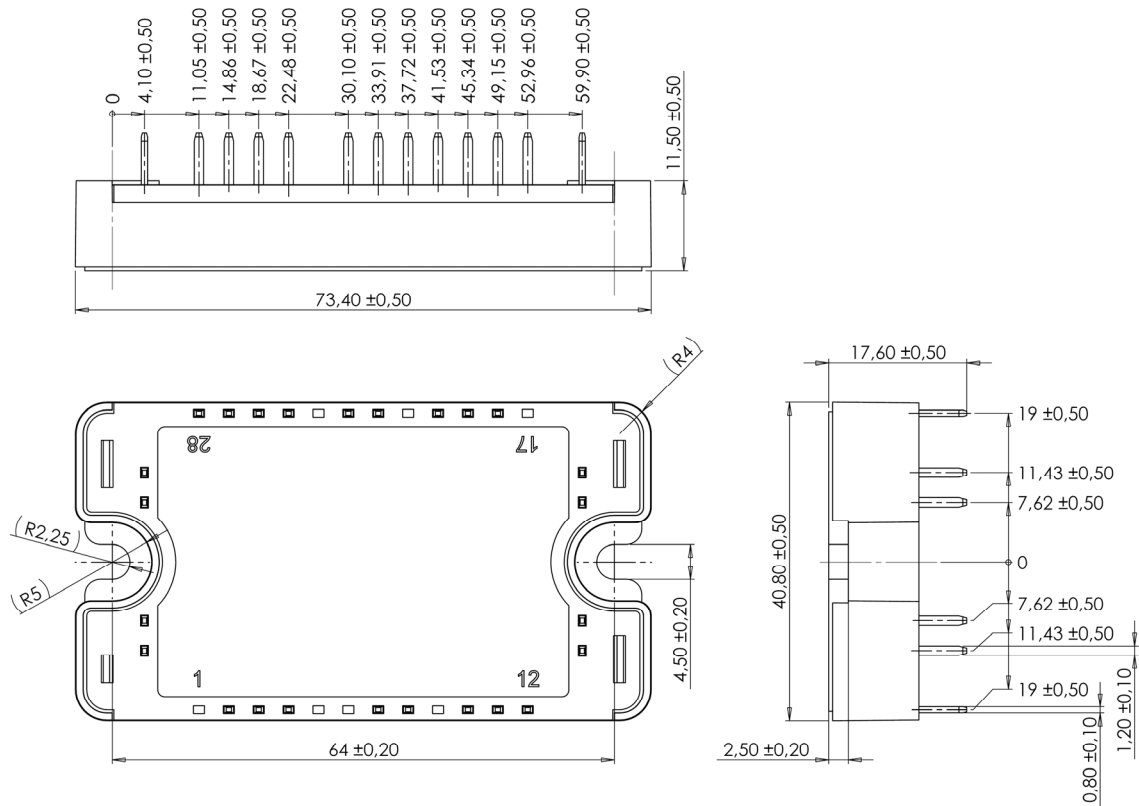
Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance			0.35	°C/W	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight			110		g

**Temperature sensor NTC** (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>			5		%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K
ΔB/B	T <sub>C</sub> = 100°C		4		%

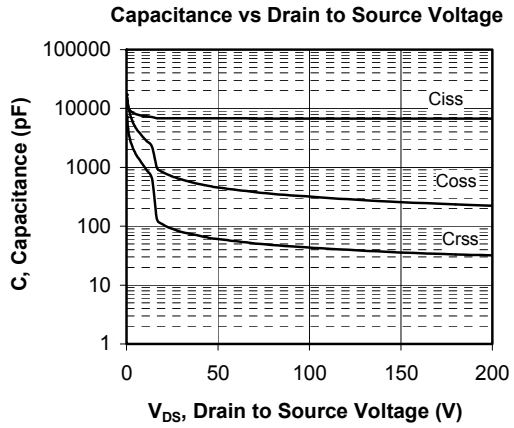
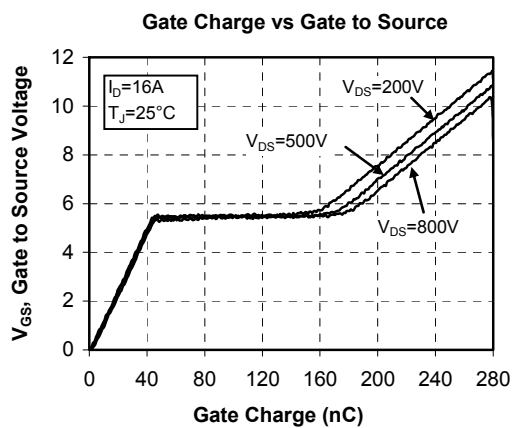
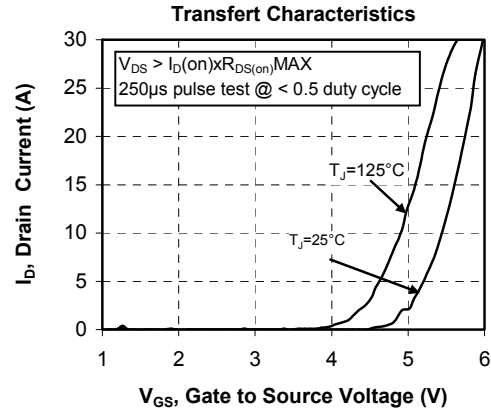
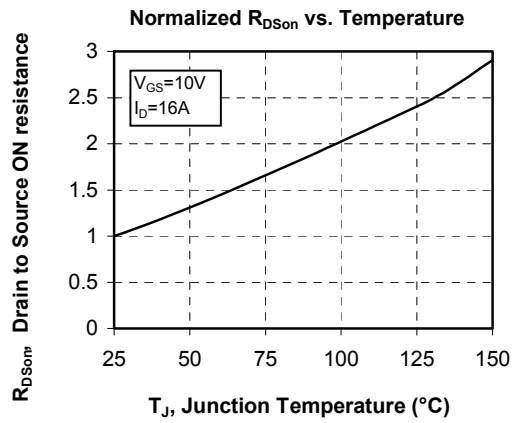
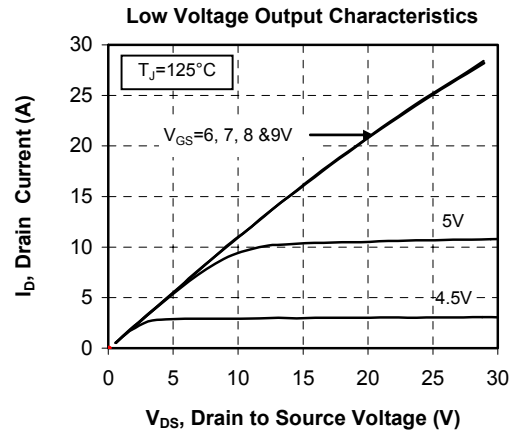
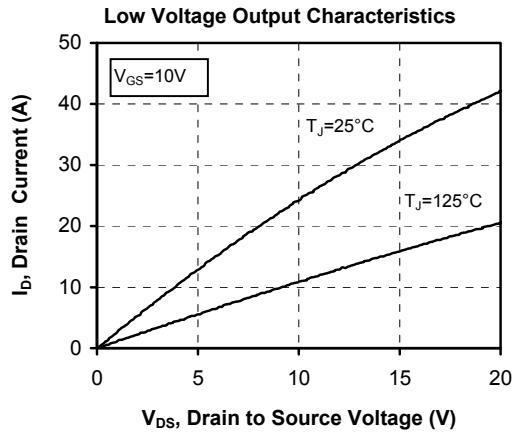
$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T} - \frac{1}{T_{25}} \right) \right]}$$

T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

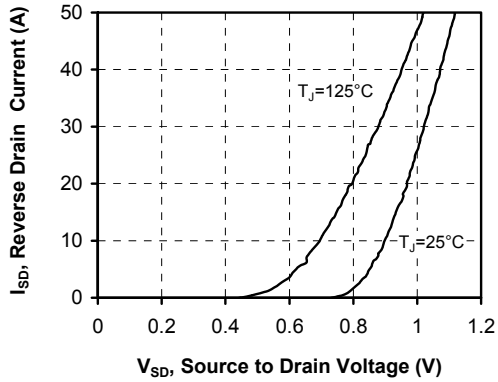
**SP3 Package outline** (dimensions in mm)


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

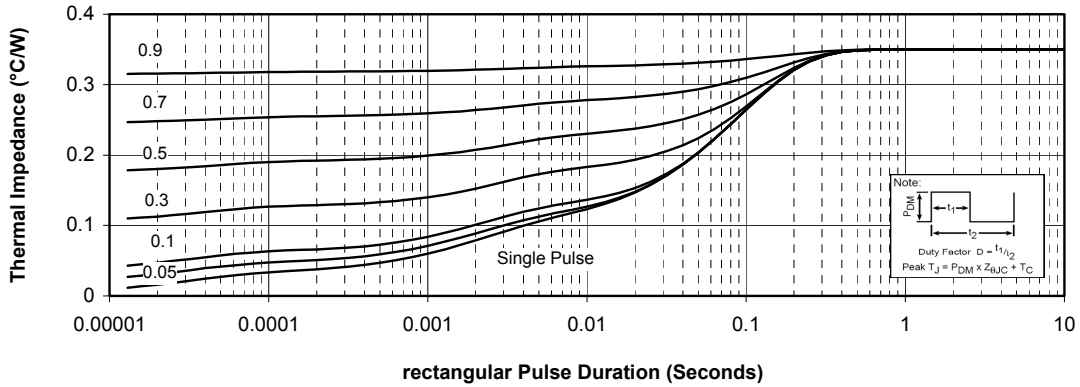
## Typical Performance Curve



**Drain Current vs Source to Drain Voltage**



**Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration**



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